

Konstantinos Zekentes

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Progress in SiC nanowire field-effect-transistors for integrated circuits and sensing applications. <i>Microelectronic Engineering</i> , 2022, 255, 111704.	1.1	15
2	Comparison of Impact Ionization Models for 4H-SiC Along the $\langle 0001 \rangle$ Direction, Through Breakdown Voltage Simulations at Room Temperature. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 2582-2586.	1.6	2
3	Compact Modeling of SiC and GaN Junction FETs at High Temperature. <i>Materials Science Forum</i> , 2019, 963, 683-687.	0.3	2
4	Direct growth of thick AlN layers on nanopatterned Si substrates by cantilever epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1600363.	0.8	14
5	Modelling of 4H-SiC VJFETs with Self-Aligned Contacts. <i>Materials Science Forum</i> , 2016, 858, 913-916.	0.3	3
6	4H-SiC VJFETs with Self-Aligned Contacts. <i>Materials Science Forum</i> , 2015, 821-823, 793-796.	0.3	3
7	TCAD models of the temperature and doping dependence of the bandgap and low field carrier mobility in 4H-SiC. <i>Microelectronic Engineering</i> , 2014, 116, 65-71.	1.1	29
8	The Formation of New Periodicities after N-Implantation in 4H- and 6H-SiC Samples. <i>Materials Science Forum</i> , 2013, 740-742, 447-450.	0.3	0
9	Fabrication Issues of 4H-SiC Static Induction Transistors. <i>Materials Science Forum</i> , 2012, 717-720, 1049-1052.	0.3	6
10	Material Limitations for the Development of High Performance SiC NWFETs. <i>Materials Science Forum</i> , 2012, 711, 70-74.	0.3	2
11	Rectifying Source and Drain Contacts for Effective Carrier Transport Modulation of Extremely Doped SiC Nanowire FETs. <i>IEEE Nanotechnology Magazine</i> , 2011, 10, 980-984.	1.1	14
12	Schottky Barrier 3C-SiC Nanowire Field Effect Transistor. <i>Materials Science Forum</i> , 2011, 679-680, 613-616.	0.3	2
13	Field Effect Transistors Based on Catalyst-Free Grown 3C-SiC Nanowires. <i>Materials Science Forum</i> , 2010, 645-648, 1235-1238.	0.3	7
14	Effect of Source and Drain Contacts Schottky Barrier on 3C-SiC Nanowire FETs I-V Characteristics. <i>Materials Science Forum</i> , 2009, 615-617, 235-238.	0.3	6
15	Fabrication and Characterization of Cr-Based Schottky Diode on n-Type 4H-SiC. <i>Materials Science Forum</i> , 2009, 615-617, 651-654.	0.3	3
16	Si nanowire p-FET with asymmetric source-drain characteristics. <i>Solid State Communications</i> , 2009, 149, 461-463.	0.9	7
17	3C-Silicon Carbide Nanowire FET: An Experimental and Theoretical Approach. <i>IEEE Transactions on Electron Devices</i> , 2008, 55, 1970-1976.	1.6	45
18	Microwave Modulators Based on 4H-SiC p-i-n Diodes. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2008, 56, 803-808.	2.9	1

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19	Fabrication of Ion-Implanted Si Nanowire p-FETs. Journal of Physical Chemistry C, 2008, 112, 13287-13291.	1.5	9
20	Theoretical comparison of 3C-SiC and Si nanowire FETs in ballistic and diffusive regimes. Nanotechnology, 2007, 18, 475715.	1.3	24
21	Microwave p-i-n Diodes Fabricated on 4H-SiC Material Grown by Sublimation Epitaxy in Vacuum. Materials Science Forum, 2007, 556-557, 933-936.	0.3	0
22	Microwave p-i-n Diodes and Switches Based on 4H-SiC. Materials Science Forum, 2007, 556-557, 999-1002.	0.3	0
23	Comparison between Schottky Diodes with Oxide Ramp Termination on Silicon Carbide and Diamond. Materials Science Forum, 2007, 556-557, 865-868.	0.3	0
24	Coupling between the Raman Spectroscopy and Photoemission Microscopy Techniques: Investigation of Defects in Biased 4H-SiC pin Diodes. Materials Science Forum, 2007, 556-557, 909-912.	0.3	0
25	Microwave p-i-n diodes and switches based on 4H-SiC. , 2006, , .		1
26	CM-Wave Modulator with High-Voltage 4H SiC pin Diodes. Materials Science Forum, 2006, 527-529, 1379-1383.	0.3	1
27	Investigation of Packaged High-Voltage 4H SiC pin Diodes in the 20-700 Å°C Temperature Range. Materials Science Forum, 2006, 527-529, 1375-1378.	0.3	5
28	Photoemission of 4H-SiC pin-Diodes Epitaxied by the Sublimation Method. Materials Science Forum, 2006, 527-529, 391-394.	0.3	2
29	Forward-Bias Degradation in 4H-SiC p ⁺ n ⁺ Diodes: Influence of the Mesa Etching. Materials Science Forum, 2005, 483-485, 773-776.	0.3	7
30	Electrochemical C-V Profiling of n-Type 4H-SiC. Materials Science Forum, 2004, 457-460, 681-684.	0.3	3
31	Low Voltage Silicon Carbide Zener Diode. Materials Science Forum, 2004, 457-460, 1029-1032.	0.3	4
32	Current Transport Mechanisms in 4H-SiC PiN Diodes. Materials Science Forum, 2004, 457-460, 1017-1020.	0.3	4
33	Simulation and Prototype Fabrication of Microwave Modulators with 4H-SiC p-i-n Diodes. Materials Science Forum, 2004, 457-460, 1089-1092.	0.3	9
34	Theoretical Investigations of Microwave Characteristics of Tunnel Diodes Made of Silicon Carbide. Materials Science Forum, 2004, 457-460, 977-980.	0.3	0
35	4H-SiC pn Diode Grown by LPE Method for High-Power Applications. Materials Science Forum, 2003, 433-436, 867-870.	0.3	0
36	Reliability of 4H-SiC p-n Diodes on LPE Grown Layers. Materials Science Forum, 2003, 433-436, 929-932.	0.3	1

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37	Use of Laser Interferometry and Optical Emission Spectroscopy for Monitoring the Reactive Ion Etching of 6H - and 4H-SiC. Materials Science Forum, 2003, 433-436, 693-696.	0.3	0
38	Pd-Based Ohmic Contacts to LPE 4H-SiC with Improved Thermal Stability. Materials Science Forum, 2003, 433-436, 713-716.	0.3	3
39	Reliable Ohmic Contacts to LPE p-Type 4H-SiC for High-Power p-n Diode. Materials Science Forum, 2002, 389-393, 917-920.	0.3	4
40	4H-SiC IMPATT Diode Fabrication and Testing. Materials Science Forum, 2002, 389-393, 1353-1358.	0.3	27
41	Photon Emission Analysis of Defect-Free 4H-SiC pn Diodes in Avalanche Regime. Materials Science Forum, 2002, 389-393, 1293-1296.	0.3	6
42	Growth and Characterization of Three-Dimensional SiC Nanostructures on Si. Materials Science Forum, 2002, 389-393, 747-750.	0.3	8
43	X-band Silicon Carbide IMPATT Oscillator. Materials Research Society Symposia Proceedings, 2001, 680, 1.	0.1	2
44	Improved Al/Si ohmic contacts to p-type 4H-SiC. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 80, 374-377.	1.7	12
45	In Situ RHEED Studies on the Influence of Ge on the Early Stages of SiC on Si(111) and (100) Surfaces. Materials Science Forum, 2001, 353-356, 187-190.	0.3	1
46	Origin of the Excellent Thermal Stability of Al/Si-Based Ohmic Contacts to p-Type LPE 4H-SiC. Materials Science Forum, 2001, 353-356, 251-254.	0.3	2
47	Silicon Carbide Zener Diodes. Materials Science Forum, 2001, 353-356, 735-738.	0.3	6
48	Electrochemical Characterization of p-Type Hexagonal SiC. Materials Science Forum, 2001, 353-356, 619-622.	0.3	5
49	Isothermal I-V Characteristics of 4H-SiC p-n Diodes with Low Series Differential Resistivity at Avalanche Breakdown. Materials Research Society Symposia Proceedings, 2000, 622, 181.	0.1	2
50	Structural and Morphological Characterization of Al/Ti-Based Ohmic Contacts on p-Type 4H-SiC Annealed Under Various Conditions. Materials Science Forum, 2000, 338-342, 1017-1020.	0.3	9
51	Electrochemical C-V Profiling of P-type 6H-SiC. Materials Science Forum, 2000, 338-342, 1061-1064.	0.3	9
52	Electrical transport quantum effects in the In _{0.53} Ga _{0.47} As/In _{0.52} Al _{0.48} As heterostructure on silicon. Journal of Applied Physics, 1994, 76, 1948-1950.	1.1	2
53	TEM analysis of InGaAs/InAlAs epitaxial layers grown over InP patterned substrates. Materials Letters, 1994, 21, 371-375.	1.3	0
54	Temperature dependence of the photoreflectance of strained and lattice-matched InGaAs/InAlAs single quantum wells. Applied Surface Science, 1993, 63, 172-176.	3.1	5

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55	Characterization of lattice-matched and strained GaInAs/AlInAs HEMT structures by photoluminescence spectroscopy. Applied Surface Science, 1993, 63, 182-186.	3.1	14
56	Photo-induced current transient spectroscopy of Al _{0.48} In _{0.52} As semi-insulating layers grown on InP by molecular beam epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1993, 22, 93-96.	1.7	4
57	Room temperature photoreflectance as a powerful tool to characterize the crystalline quality of InAlAs layers grown on InP substrates. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1993, 21, 177-180.	1.7	2
58	Materials problems for the development of InGaAs/InAlAs HEMT technology. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1993, 20, 21-25.	1.7	1
59	Room-temperature photoreflectance as an efficient tool for study of the crystalline quality of InAlAs layers grown on InP substrates. Applied Physics Letters, 1993, 63, 1654-1656.	1.5	3
60	Frequency-Resolved Admittance Measurements on InAlAs/InGaAs/InAlAs Single-Quantum Wells to Determine the Conduction Band Offset and the Capture Coefficient. Journal of the Electrochemical Society, 1993, 140, 1492-1495.	1.3	9
61	Photoreflectance studies of lattice-matched and strained InGaAs/InAlAs single quantum wells. Journal of Applied Physics, 1993, 74, 1437-1439.	1.1	16
62	Observation of metastable effects in pseudomorphic heterostructures InCaAs/InAlAs. High Pressure Research, 1992, 9, 97-100.	0.4	0
63	Electrical transport study of pseudomorphic heterostructures InGaAs-InAlAs on Si and InP substrates. Sensors and Actuators A: Physical, 1992, 33, 67-70.	2.0	0
64	Optical properties of InGaAs films embedded in plasma etched InP wells. Applied Physics Letters, 1992, 61, 798-800.	1.5	4
65	Asymmetric Fabry-Perot p-i-n multiple quantum well optical modulators grown on silicon and GaAs substrates. Superlattices and Microstructures, 1992, 12, 145-149.	1.4	1
66	Growth of SiC Microwires through Si Microwires Carburization. Materials Science Forum, 0, 679-680, 512-515.	0.3	1
67	Room Temperature Physical Characterization of Implanted 4H- and 6H-SiC. Materials Science Forum, 0, 717-720, 589-592.	0.3	1
68	Si NWs Conversion to Si-SiC Core-Shell NWs by MBE. Materials Science Forum, 0, 821-823, 965-969.	0.3	0
69	Comparison of Bottom-Up and Top-Down 3C-SiC NWFETs. Materials Science Forum, 0, 858, 1001-1005.	0.3	5
70	Salicide-Like Process for the Formation of Gate and Source Contacts in 4H-SiC TSI-VJFETs. Materials Science Forum, 0, 897, 407-410.	0.3	3
71	Capacitances in 4H-SiC TSI-VJFETs. Materials Science Forum, 0, 897, 591-594.	0.3	1
72	A Continuous Semi-Empirical VJFET Capacitance Model from Sub to above Threshold Regime. Materials Science Forum, 0, 924, 649-652.	0.3	0

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73	Cross-Section Doping Topography of 4H-SiC VJFETs by Various Techniques. Materials Science Forum, 0, 924, 653-656.	0.3	1
74	On the Optimum Determination and Use of SiC VJFET Threshold Voltage. Materials Science Forum, 0, 924, 657-660.	0.3	1
75	4H-SiC p-Type Doping Determination from Secondary Electrons Imaging. Materials Science Forum, 0, 963, 328-331.	0.3	0